

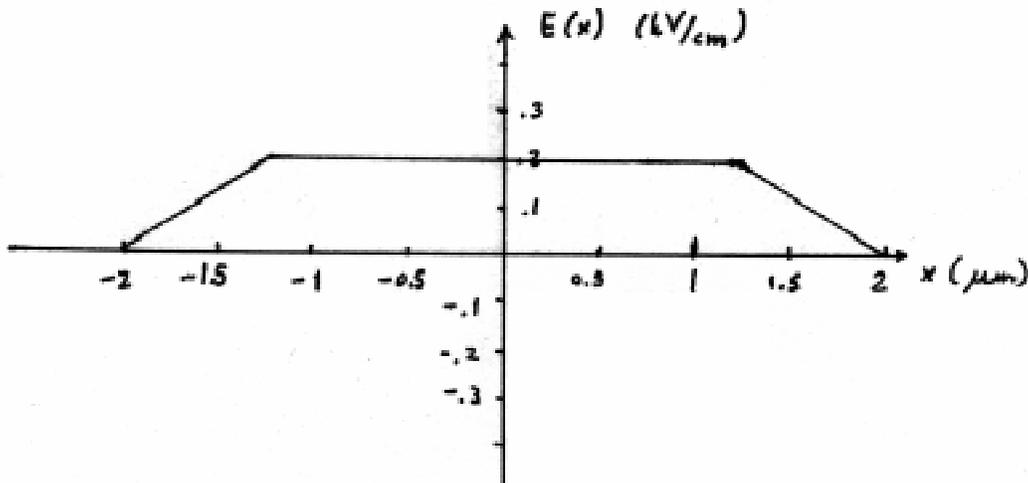
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Problem Set #3
 Due Wednesday, September 16th, 1998

EECS105

FALL 1998

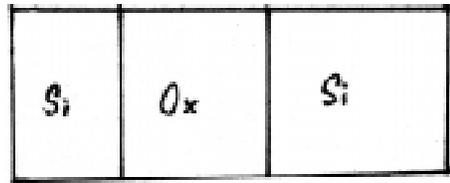
1. You are in charge of the new line of Silicon Spice's line of E-field creation machines. Your stock options have decreased from \$50 last October to \$23 3/4 as of close on Friday. Luckily, you've just created a machine that can generate the following E-field distribution in silicon:



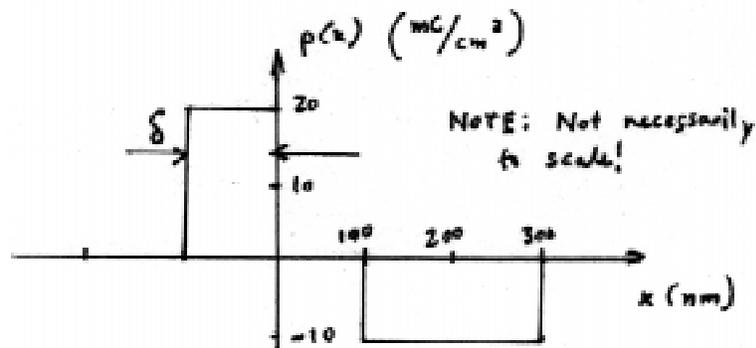
- a. What would the charge density $\rho(x)$ look like?
 - b. Assume that the potential at $\phi(-2 \mu\text{m}) = -500 \text{ mV}$. What is the potential at $x = 0 \mu\text{m}$? How about at $x = 2 \mu\text{m}$? HINT: do you *really* need to solve for the potential function to answer this?
 - c. Using the same assumption that the potential at $\phi(-2 \mu\text{m}) = -500 \text{ mV}$, sketch the potential $\phi(x)$.
2. Argh, another urgent email from your manager: she needs a $500 \pm 150 \text{ fF}$ tunable capacitor NOW, built via a reverse biased pn junction. You email the process engineer to get some idea of the process flow. She tells you that with the latest $.18 \mu\text{m}$ technology, they are doping the Si with $N_a = 10^{16} \text{ cm}^{-3}$, $N_d = 10^{18} \text{ cm}^{-3}$.
- a. First, figure out what the capacitance per unit area (in $\text{fF}/\mu\text{m}^2$) is for $V_D = 0 \text{ V}$.
 - b. How much area do we need for our capacitor? What is the voltage range do we need to be able to tune it over the entire range? HINT: $V_D = 0 \text{ V}$ must correspond to $C = 650 \text{ fF}$, the maximum capacitance.

(over)

3. You are a process engineer in charge of designing silicon oxide "sandwiches". They look like this:



- a. Under some biasing potential, the charge density looks like the following sketch. How wide should δ be to ensure electrical neutrality?



- b. Figuring you need some practice using boundary conditions, your boss asks you to derive the numerical value of the E-field at $x = 50$ nm and $x = 200$ nm.
- c. If you got part (b), this should be relatively easy...please sketch $E(x)$.

Please visit our web site: <http://www-inst.EECS.Berkeley.EDU/~ee105/>

Please post your questions on our newsgroup: ucb.class.ee105

Please return your homework in 558 Cory Hall, to Cheryl Craigwell (cmc@eeecs, 642-1237, fax 642-2739), or in class by 11:10am of the due date. Late homeworks will not be graded.